

/ Descriptions

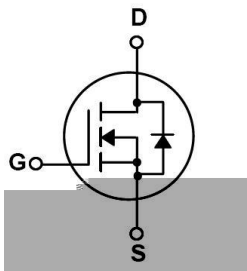
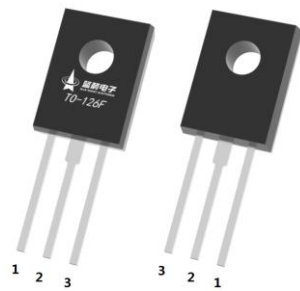
TO-126F N MOS
N-CHANNEL MOSFET in a TO-126F Plastic Package.

/ Features

Low gate charge, low crss, fast switching.

/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit**/ Pinning**

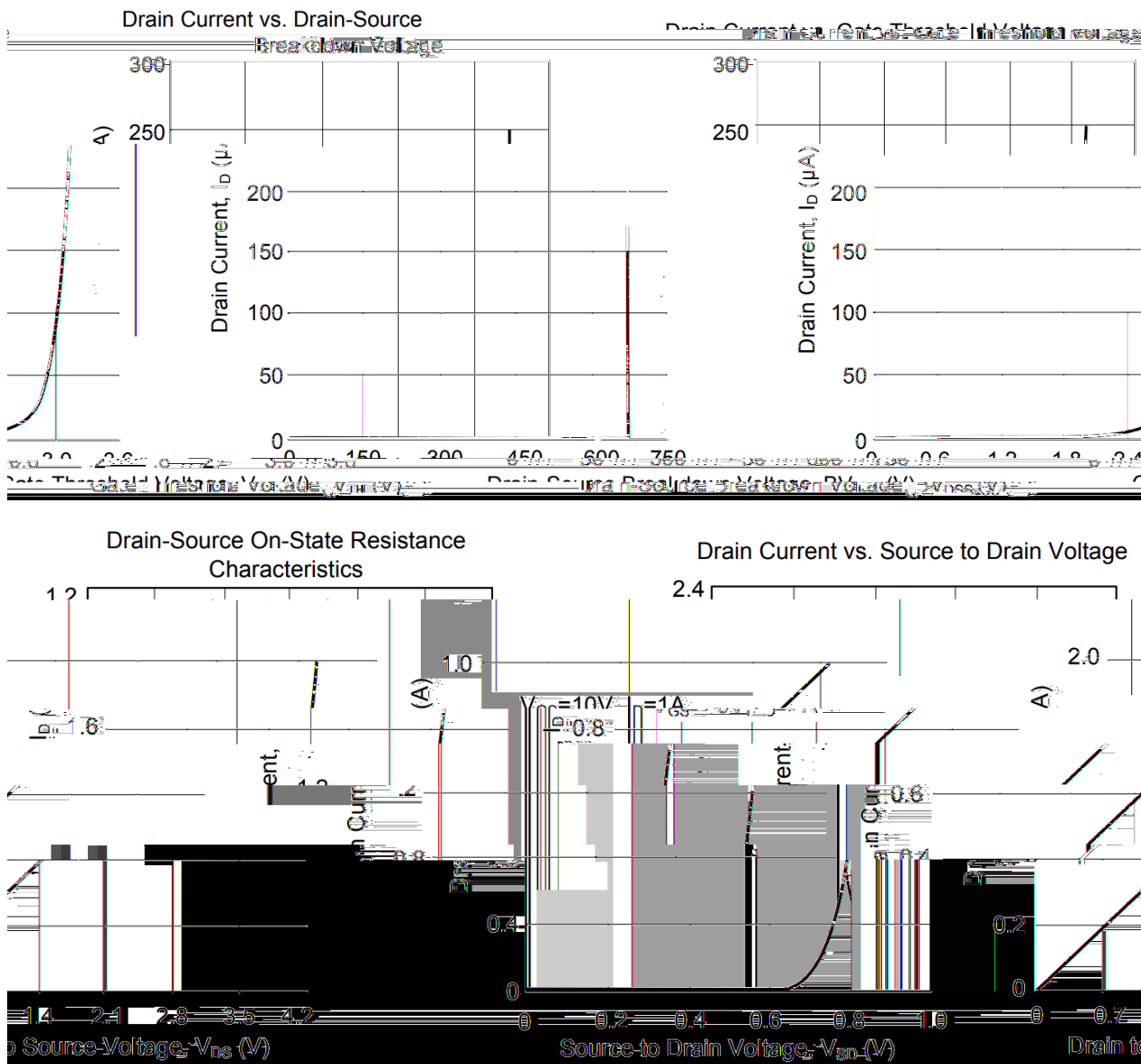
PIN1 G PIN 2 D PIN 3 S

/ h_{FE} Classifications & Marking

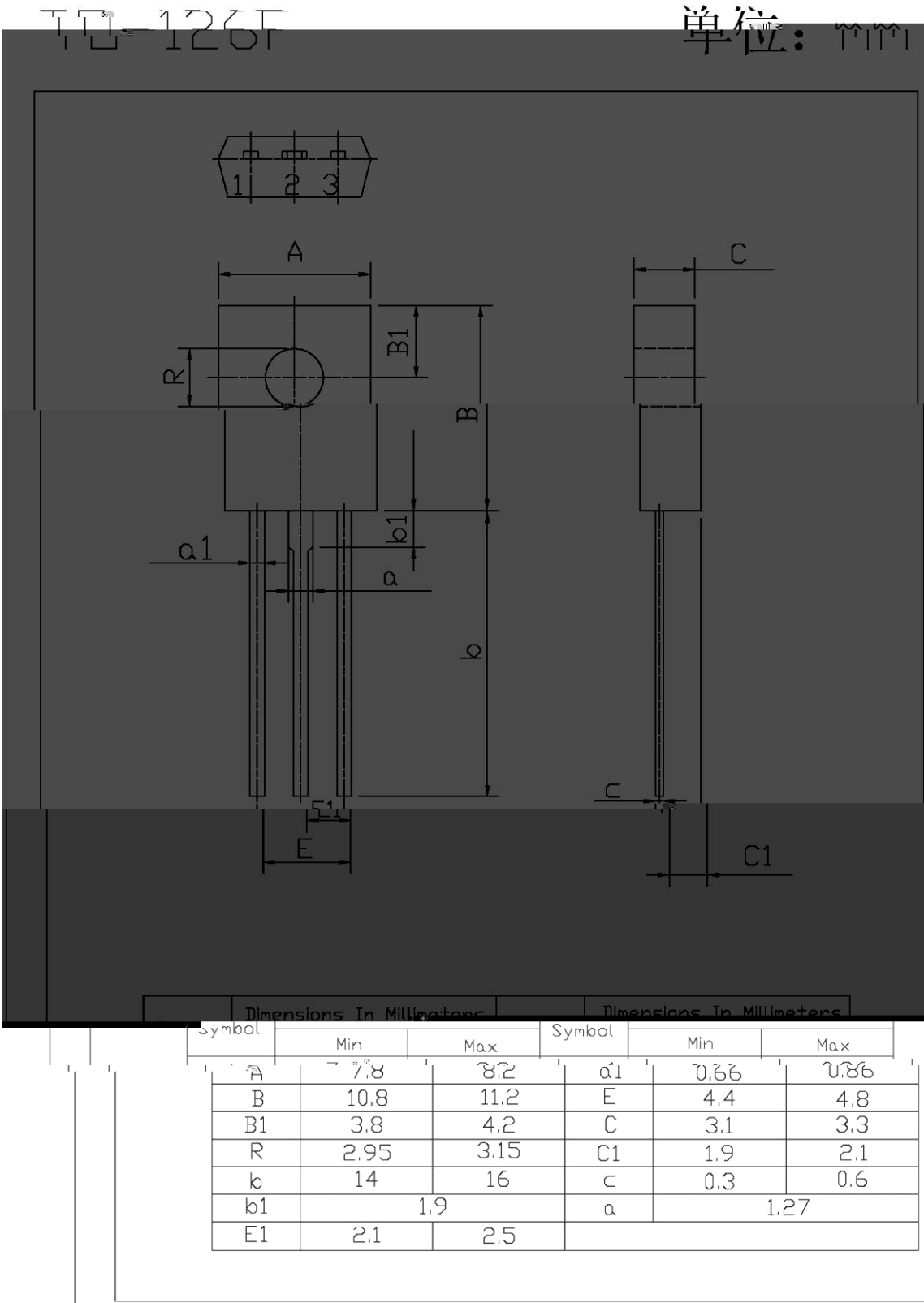
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_c=25^{\circ}\text{C})$	2.0	A
Drain Current	$I_D(T_c=100^{\circ}\text{C})$	1.3	A
Drain Current - Pulsed	I_{DM}	6.0	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	39	mJ
Avalanche Current	I_{AR}	3.0	A

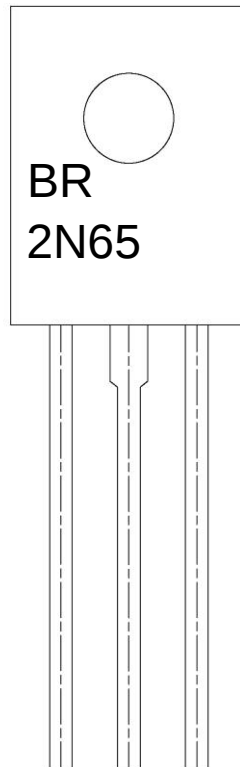
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

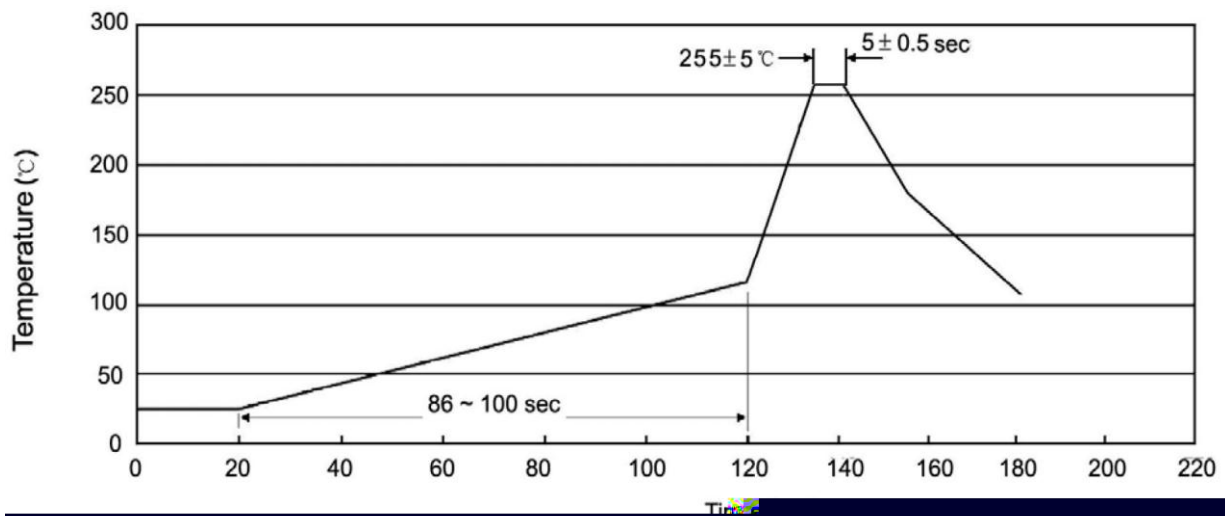
Note:

BR: Company Code

2N65: Product Type.

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm ³)